EAST Search History

EAST Search History (Prior Art)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	(@ad<="19950130") and via and "etch stop" and "hard mask" and cinductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:00
S2	11	(@ad<="19950130") and via and "etch stop" and "hard mask" and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:50
S3	2	("5328533").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S4	2	("5328553").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:05
S5	19	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:51
S6	8	(@ad<="19950130") and via and ("etch stop" or etchstop) and ("hard mask" or hardmask) and conductor not S2	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:52
S7	21	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulator or dielectric)) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53

S8	29	(@ad<="19950130") and via and ("etch stop" or etchstop) and (fourth with (insulat$3 or dielectric)) and conductor	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/01/04 13:53
S9	2	("5328553").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:50
S10	2	("20040175952").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:52
S11	5520	(@ad<="19950130") and (438/69$.ccls.)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S12	428	(@ad<="19950130") and (438/69$.ccls.) and via	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:58
S13	32	(@ad<="19950130") and (438/69$.ccls.) and via and ("etch stop" or etchstop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 15:59
S14	2	("5240871").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:13
S15	6673	(@ad<="19950130") and ((nitride with etch$3) same (oxide with etch$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:41
S16	906	(@ad<="19950130") and ((nitride near2 etch$3) same (oxide near2 etch$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42

S17	641	(@ad<="19950130") and ((nitride near2 etch$3) with (oxide near2 etch$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:42
S18	2	("4385937").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 16:57
S19	215	(@ad<="19950130") and ((nitride near2 etch$3) with (oxide near2 etch$3)) and (memory or storage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/24 17:20
S20	22	(Doan-Trung.in.) or ("Cathey-David.in")	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:18
S21	402	(@ad<="19950130") and ("438"/$.ccls.) and via and ("etch stop" or etchstop)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:22
S22	99	(@ad<="19950130") and ("438"/$.ccls.) and via and ("etch stop" or etchstop) and (memory or storage)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/07/25 06:23
S23	3	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (via or trench)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:20
S24	5	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:28

S25	2	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (etch$3) not S23	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:29
S26	0	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (damascene)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:32
S27	7	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulat$4 or isolat$3)) and (second near2 (dielectric or insulat$4 or isolat$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S28	7	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulat$4 or isolat$3)) and (second near2 (dielectric or insulat$4 or isolat$3)) and (etch)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:33
S29	19	(@ad<="19950130") and (first near2 (dielectric or insulat$4 or isolat$3)) and (second near2 (dielectric or insulat$4 or isolat$3)) and (etch$3) and damascene	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 09:56
S30	126	(@ad<="19950130") and (storage or dram or memory) and alignemene	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:18
S31	4	(@ad<="19950130") and (storage or dram or memory) and (alignemene with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:19

S32	8855	(@ad<="19950130") and (storage or dram or memory) and (aligned with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:20
S33	689	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:21
S34	274	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and (first near2 (dielectric or insulat$4 or isolat$3)) and (second near2 (dielectric or insulat$4 or isolat$3)) and (etch$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:24
S35	136	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat$4 or isolat$3)) and (second near2 (dielectric or insulat$4 or isolat$3)) with (etch$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S36	69	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat$4 or isolat$3)) with (second near2 (dielectric or insulat$4 or isolat$3)) with (etch$3))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:25
S37	18	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat$4 or isolat$3)) with (second near2 (dielectric or insulat$4 or isolat$3)) with (etch$3) with (third near2 (dielectric or insulat$4 or isolat $3)))	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:26

S38	3	(@ad<="19950130") and (storage or dram or memory) and (aligned with self with (hole or via or contact)) and ((first near2 (dielectric or insulat$4 or isolat$3)) with (second near2 (dielectric or insulat$4 or isolat$3)) with (etch$3) with (third near2 (dielectric or insulat$4 or isolat $3))) and stop	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 12:28
S39	32	("4252840" | "4758528" | "4974040" | "5150278" | "5196910" | "5240871" | "5281549" | "5292677" | "5324681" | "5328553" | "5338700" | "5476806" | "5479054" | "5502336" | "5605857" | "6744091").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 13:30
S40	2	("20040175952").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50
S41	1	S40 and (fourth with insulation with side$1wall with conductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/30 14:50
S42	54	(EMA-T$).in. and insulation. clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:19
S43	31	(EMA-T$).in. and insulation. clm. and step.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:19
S44	24	(EMA-T$).in. and insulation. clm. and step.clm. and etching.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:20
S45	8	(EMA-T$).in. and insulation. clm. and step.clm. and etching.clm. and stopper.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/12/31 10:20

S46	4	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor near2 memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:38
S47	4	(@ad<="19950130") and (etch$3 near1 stop) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:45
S48	4	(@ad<="19950130") and (etch$3 near1 stop$4) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:46
S49	5	(@ad<="19950130") and (etch$3 near1 stop$4) and (hardmask or hard$1mask) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:47
S50	1	(@ad<="19950130") and (etch$3 near1 stop$4) and (hardmask or hard$1mask) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:47
S51	1	(@ad<="19950130") and (etch$3 near2 stop$4) and (hardmask or hard$1mask) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:51
S52	418	(@ad<="19950130") and (etch$3 near2 stop$4) and (transistor with memory) not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 12:58
S53	324	(@ad<="19950130") and (etch$3 near2 stop$4) and (transistor with memory) and mask and contact not S48	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:05

S54	307	(@ad<="19950130") and (etch$3 near2 stop$4) and (transistor with memory) and mask and contact not S48 and insulat$3	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:06
S55	62	(@ad<="19950130") and (etch$3 near2 stop$4) and (transistor with memory) and mask and contact not S48 and (insulat$3 with fourth)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:06
S56	27	(@ad<="19950130") and (etch$3 near2 stop$4) and (transistor with memory) and mask and contact not S48 and (insulat$3 with fourth with etch$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 13:11
S57	3	(anezaki-t$).in. and insulation.clm. and step.clm. and etching.clm. and stopper.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:19
S58	194	("257"/$).ccls. and insulation.clm. and step.clm. and etching.clm. and stopper.clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:20
S59	57	("257"/$).ccls. and insulation.clm. and step.clm. and etching.clm. and stopper.clm. and (memory with transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:21
S60	63	("257"/$).ccls. and insulation.clm. and step.clm. and etching.clm. and (etch$3 near1 stop$3).clm. and (memory with transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:22
S61	88	("257"/$).ccls. and insulation.clm. and contact.clm. and etching.clm. and (etch$3 near1 stop$3).clm. and (memory with transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:22
S62	349	("257"/$).ccls. and ((insulat$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch$3 near1 stop $3).clm. and (memory with transistor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:24

S63	0	(438/692).ccls. and ((insulat $3 or dielectric) with (first and second and fourth)).clm. and contact.clm. and etching. clm. and (etch$3 near1 stop $3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 14:28
S68	1	(438/694).ccls. and ((insulat $3 or dielectric) with (first and second and fourth)).clm. and contact.clm. and etching. clm. and (etch$3 near1 stop $3).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:41
S69	1038	(438/633).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:42
S70	3350	(438/692).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S71	4413	(438/694).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S72	619	(438/397).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S73	391	(438/715).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:43
S74	70	(257/E21.017).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S75	1267	(257/E21.575).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44

S76	1445	(216/18).ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S77	12050	S69 S70 S71 S72 S73 S74 S75 S76	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2009/11/25 15:44
S78	4	(@ad<="19950130") and (etch$3 near1 stop$4) and (hardmask or hard$1mask) and (first near2 (dielectric or insulator or insulation)) and (second near2 (dielectric or insulator or insulation)) and (transistor with memory)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 15:45
S79	5	(@ad<="19950130") and S77 and (etch$3 near2 stop$4) and (transistor with memory) and mask and contact not S78 and (insulat$3 with fourth with etch$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2009/11/25 15:45

EAST Search History (Interference)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S64	3	(438/692).ccls. and ((insulat$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch$3 near1 stop$3).clm. and (memory with transistor)	USPAT; UPAD	OR	OFF	2009/11/25 14:25
S65	23	(438/692).ccls. and ((insulat$3 or dielectric) with first).clm. and contact.clm. and etching.clm. and (etch$3 near1 stop$3).clm.	USPAT; UPAD	OR	OFF	2009/11/25 14:26
S66	20	(438/692).ccls. and ((insulat$3 or dielectric) with (first and second)).clm. and contact.clm. and etching.clm. and (etch$3 near1 stop$3).clm.	USPAT; UPAD	OR	OFF	2009/11/25 14:27

| S67 | 0 | (438/692).ccls. and ((insulat$3 or dielectric) with (first and second and fourth)).clm. and contact. clm. and etching.clm. and (etch$3 near1 stop$3).clm. | USPAT; UPAD | OR | | OFF | 2009/11/25 14:27 |

12/3/2009 10:14:21 AM
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